



ATP202

N-Channel Power MOSFET 30V, 50A, 12mΩ, Single ATPAK

ON Semiconductor®

<http://onsemi.com>

Features

- Low ON-resistance
- 4.5V drive
- Halogen free compliance
- Large current
- Slim package
- Protection diode in

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		30	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		50	A
Drain Current (PW≤10μs)	I _{DP}	PW≤10μs, duty cycle≤1%	150	A
Allowable Power Dissipation	P _D	T _c =25°C	40	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	E _{AS}		45	mJ
Avalanche Current *2	I _{AV}		25	A

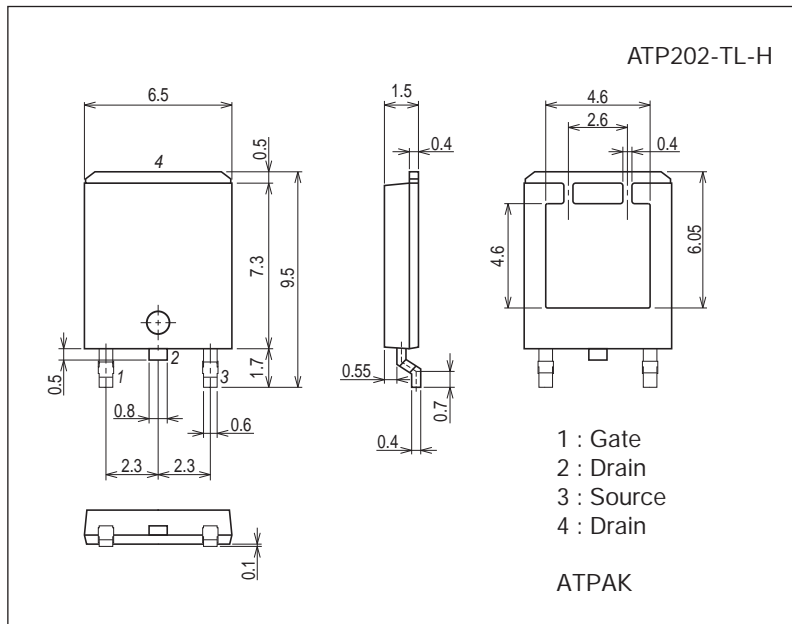
Note : *1 V_{DD}=10V, L=100μH, I_{AV}=25A
*2 L≤100μH, Single pulse

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ)

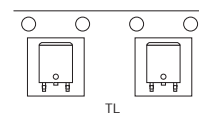
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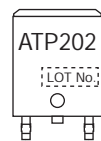
Product & Package Information

- Package : ATPAK
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

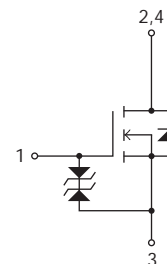
Packing Type: TL



Marking



Electrical Connection

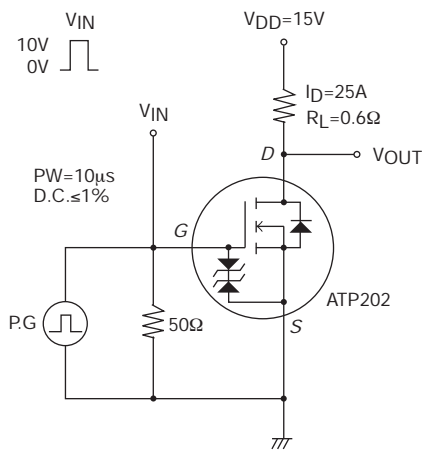


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Electrical Characteristics at Ta=25°C

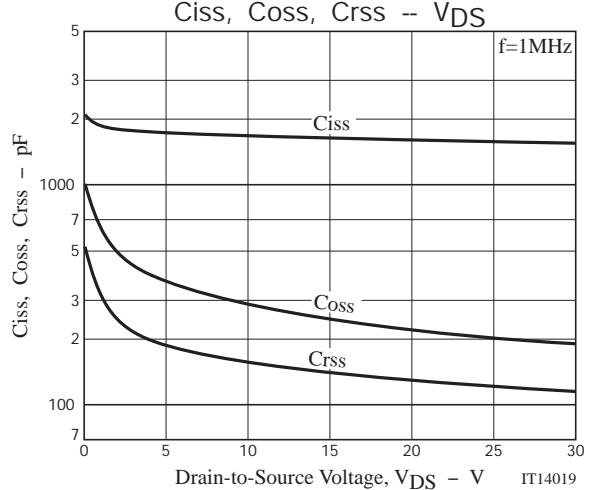
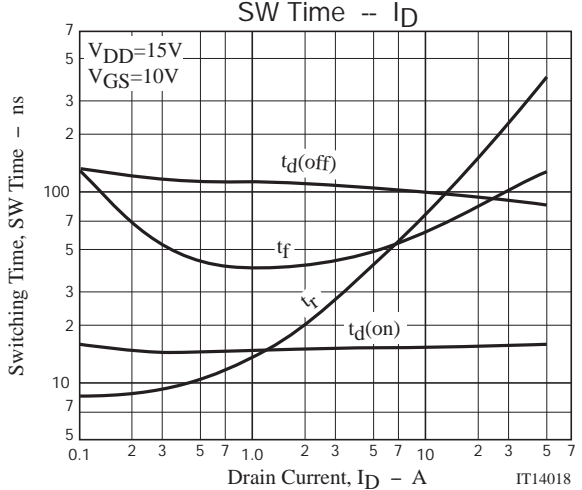
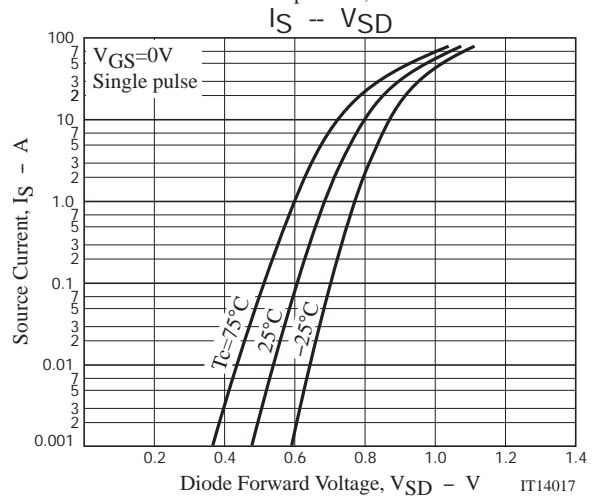
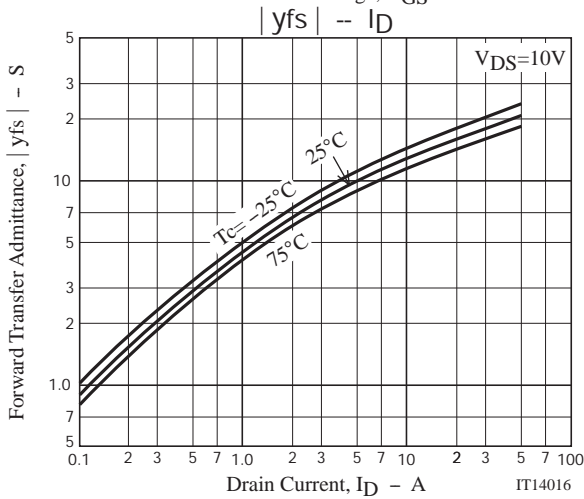
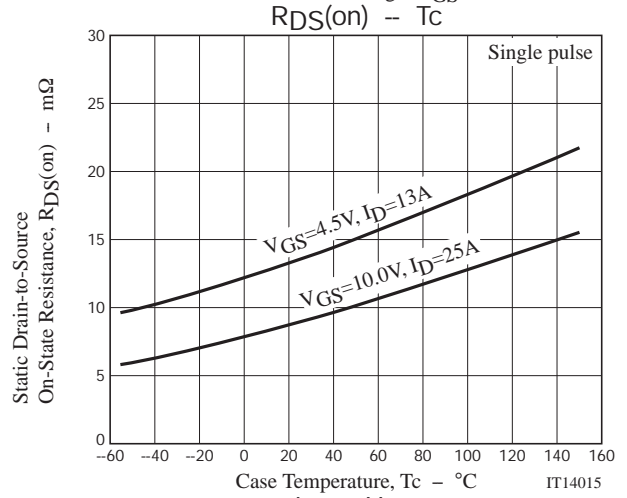
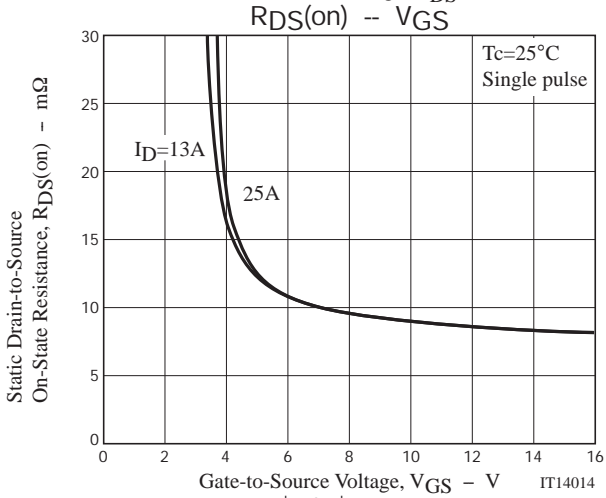
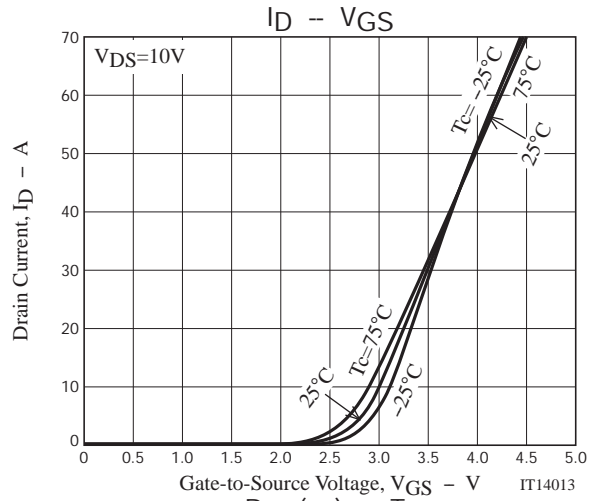
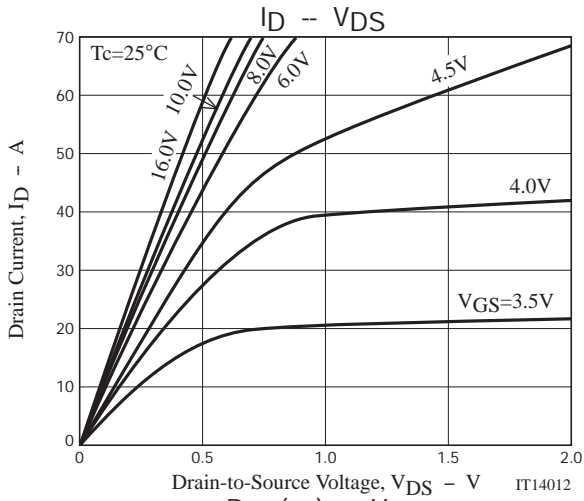
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =25A	10	17		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =25A, V _{GS} =10V		9	12	mΩ
	R _{DS(on)2}	I _D =13A, V _{GS} =4.5V		14	20	mΩ
Input Capacitance	C _{iss}	V _{DS} =10V, f=1MHz		1650		pF
Output Capacitance	C _{oss}			285		pF
Reverse Transfer Capacitance	C _{rss}			160		pF
Turn-ON Delay Time	t _{d(on)}			16		ns
Rise Time	t _r	See specified Test Circuit.		185		ns
Turn-OFF Delay Time	t _{d(off)}			93		ns
Fall Time	t _f			93		ns
Total Gate Charge	Q _g			27		nC
Gate-to-Source Charge	Q _{gs}	V _{DS} =15V, V _{GS} =10V, I _D =50A		7.5		nC
Gate-to-Drain "Miller" Charge	Q _{gd}			4		nC
Diode Forward Voltage	V _{SD}		I _S =50A, V _{GS} =0V		0.97	1.2

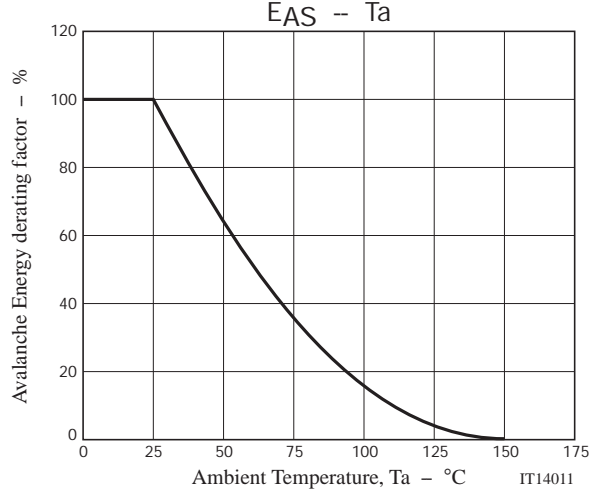
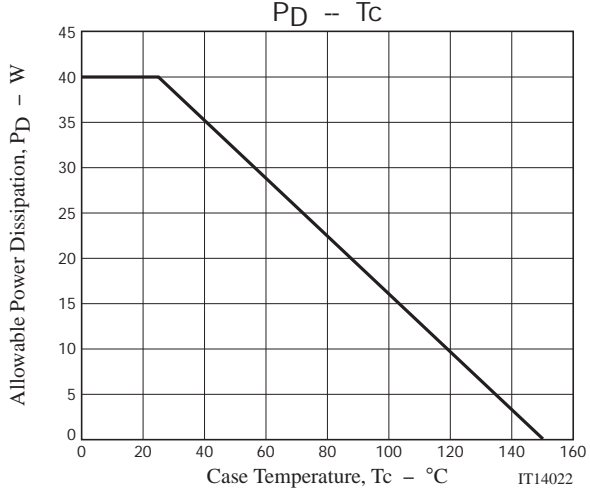
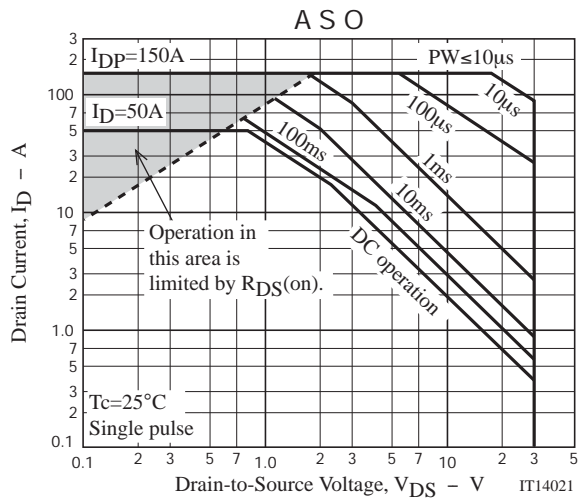
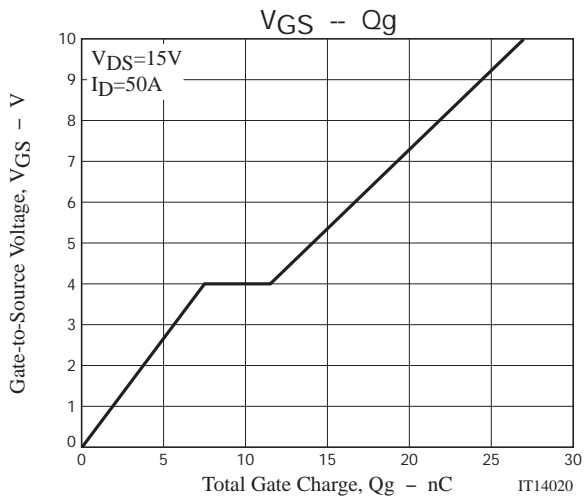
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
ATP202-TL-H	ATPAK	3,000pcs./reel	Pb Free and Halogen Free





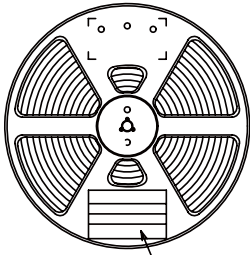
Taping Specification

ATP202-TL-H

1. Packing Format (TL)

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	INNER BOX SD-C-18	OUTER BOX SD-A-18
ATPAK	ATP	3,000	3,000	15,000	1 reels contained Dimensions:mm (external) 340×340×28	5 inner boxes contained Dimensions:mm (external) 355×355×165

Packing method



Reel label

Reel label, Inner box label
(unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

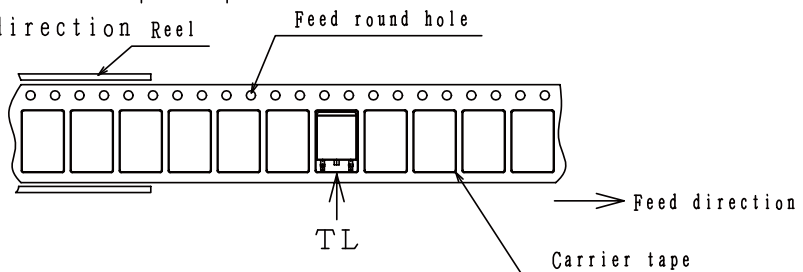
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction Reel



The one electrode terminals on feed hole side...TL

ATP202

Outline Drawing

ATP202-TL-H



Land Pattern Example



Note on usage : Since the ATP202 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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